ON Semiconductor

INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION #20307

Generic Copy

Issue Date: 06-Dec-2013

TITLE: Change to wafer size (5inch to 6inch) at ON Semiconductor fab location in Niigata, Japan.

PROPOSED FIRST SHIP DATE: 06-May-2014

AFFECTED CHANGE CATEGORY(S): Wafer Size Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:
Contact your local ON Semiconductor Sales Office or
<Minoru.Akaishi@onsemi.com>

SAMPLES:
Contact your local ON Semiconductor Sales Office or
<Takashi.Asami@onsemi.com>
<Akio.Nagahama@onsemi.com>

ADDITIONAL RELIABILITY DATA: unavailable
Contact your local ON Semiconductor Sales Office or
<Satoru.Fujinuma@onsemi.com>

NOTIFICATION TYPE:

Initial Product/Process Change Notification (IPCN)

First change notification sent to customers. IPCNs are issued at least 120 days prior to implementation of the change. An IPCN is advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan.

The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN).

This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change.

DESCRIPTION AND PURPOSE:

This is to increase our supply capacity to support increased demand. Thus to be able to continuously supply products, Wafer size will be changed from 5inch to 6inch for parts identified in this IPCN.

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QUALIFICATION PLAN:

Reliability Test was planned as below. Reliability Test Results will be provided in the FPCN.

Test Items	Test Condition	Test Time
Steady State Operating Life	Tjmax , Vcc(Vdd)opemax	1000h
Temperature Humidity Bias *	Ta=85C,RH=85%, Vcc=Recommended	1000h
Temperature Humidity Strage *	Ta=85C,RH=85%	1000h
Temperature Cycle *	Ta=-55C 30min. ⇔ Ta=150C 30min.	100cyc
Pressure Cooker *	Ta=121C,RH=100% ,205kPa	50h
High Temperature Storage	Ta=150C	1000h
Low Temperature Storage	Ta=-55C	1000h
Resistance to Soldering heat (SMD : Reflow Soldering) (THD : Flow Soldering)	(SMD) 255C,10s(Peak260C) (THD) 260C,10s	(SMD)2times (THD)1time
Electrostatic Discharge (HBM or MM)	Vcc pin versus each pin, Gnd pin versus each pin (HBM) C=100pF, R=1500ohm, V=+/-1000V (MM) C=200pF, R=0ohm, V=+/-150V	(HMB)3times (MM)1time

Note:
(SMD) The test items with * mark are put into operation after the reflow soldering (at 255C for 10 seconds)

Temperature Humidity Bias: Power Dissipation >= 0.1W (Intermittent power application consists of 1-hour ON and 3-hours OFF).

Judgment Criteria: Judgment Criteria are due to the limits of the electrical characteristics in the detail specification.

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List of affected General Parts:

LV5052V-MPB-E
LV5052V-TLM-E
LV5065VB-TLM-H
LV5069JA-AH
LV5069JA-ZH
LV5980MC-AH
LV8068V-MPB-H
LV8068V-TLM-H
LV8127T-MPB-H
LV8127T-TLM-H
LV8282PV-MPB-H
LV8282PV-TLM-H
LV8400V-MPB-E
LV8400V-TLM-E
LV8401V-MPB-E
LV8401V-TLM-E
LV8402GP-H
LV8402GP-TE-L-H
LV8402V-MPB-E
LV8402V-TLM-E
LV8548MC-AH
LV8548MCZ-AH
LV8549MC-AH
LV8711TL-MPB-H
LV8711TL-TLM-H
LV8711T-MPB-H
LV8711T-TLM-H
LV8712T-MPB-H
LV8712T-TLM-H